

**N-Channel Enhancement Mode Power MOSFET**

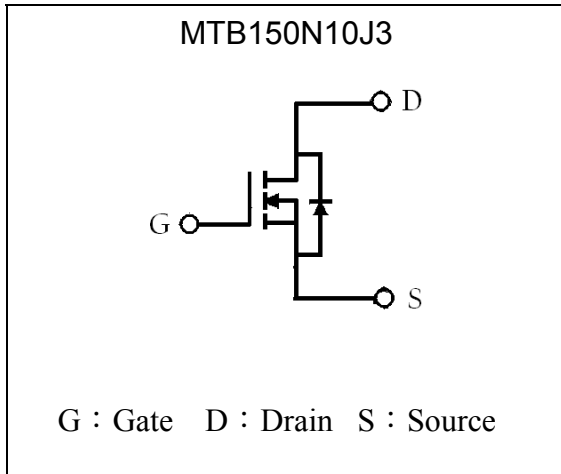
# MTB150N10J3

|   |  |        |
|---|--|--------|
| BV <sub>DSS</sub>   |  | 100V   |
| I <sub>D</sub> @ V <sub>GS</sub> =10V, T <sub>A</sub> =25°C |  | 2.3A   |
| I <sub>D</sub> @ V <sub>GS</sub> =10V, T <sub>C</sub> =25°C |  | 7A     |
| R <sub>DS(on)(TYP)</sub>                                    | V <sub>GS</sub> =10V, I <sub>D</sub> =10A  | 163 mΩ |
|   | V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A | 178 mΩ |

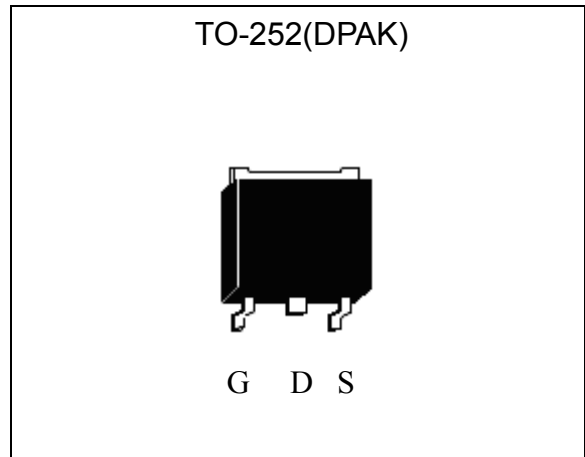
**Features**

- Single Drive Requirement
- Low On-resistance
- Fast Switching Characteristic
- Repetitive Avalanche Rated
- Pb-free lead plating and halogen-free package

**Equivalent Circuit**

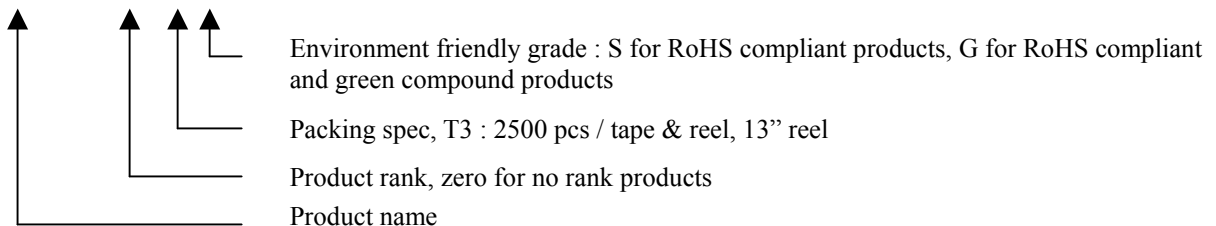


**Outline**



**Ordering Information**

| Device             | Package   | Shipping              |
|--------------------|---|-----------------------|
| MTB150N10J3-0-T3-G | TO-252<br>(Pb-free lead plating and halogen-free package) | 2500 pcs / tape& reel |





**Absolute Maximum Ratings** (Ta=25°C, unless otherwise specified)

| Parameter  | Symbol                            | Limits                | Unit   |   |
|--|-----------------------------------|-----------------------|--------|---|
| Drain-Source Voltage   | V <sub>DS</sub>                   | 100                   | V      |   |
| Gate-Source Voltage  | V <sub>GS</sub>                   | ±20                   |        |   |
| Continuous Drain Current @ V <sub>GS</sub> =10V, T <sub>C</sub> =25°C  | I <sub>D</sub>                    | 7                     | A      |   |
| Continuous Drain Current @ V <sub>GS</sub> =10V, T <sub>C</sub> =100°C |                                   | 4.4                   |        |   |
| Continuous Drain Current @ V <sub>GS</sub> =10V, T <sub>A</sub> =25°C  |                                   | 2.3                   |        |   |
| Continuous Drain Current @ V <sub>GS</sub> =10V, T <sub>A</sub> =70°C  |                                   | 1.8                   |        |   |
| Pulsed Drain Current   | I <sub>DM</sub>                   | 28 *1                 |        |   |
| Avalanche Energy @ L=1mH, I <sub>D</sub> =7A, V <sub>DD</sub> =50V     | E <sub>AS</sub>                   | 24.5 *3               | mJ     |   |
| Repetitive Avalanche Energy @ L=0.05mH                                 | E <sub>AR</sub>                   | 2.5                   |        |   |
| Total Power Dissipation  | P <sub>D</sub>                    | T <sub>C</sub> =25°C  | 25     | W |
|  |                                   | T <sub>C</sub> =100°C | 16     |   |
|  | P <sub>DSM</sub>                  | T <sub>A</sub> =25°C  | 2.5 *2 |   |
|  |                                   | T <sub>A</sub> =70°C  | 1.6 *2 |   |
| Operating Junction and Storage Temperature Range                       | T <sub>j</sub> , T <sub>stg</sub> | -55~+150              | °C     |   |

**Thermal Data**

| Parameter                                    | Symbol           | Value | Unit |
|--|------------------|-------|------|
| Thermal Resistance, Junction-to-case, max    | R <sub>θJC</sub> | 5     | °C/W |
| Thermal Resistance, Junction-to-ambient, max | R <sub>θJA</sub> | 50 *2 |      |

- Note : 1. Pulse width limited by maximum junction temperature.  
 2. Surface mounted on a 1 in<sup>2</sup> pad of 2oz copper. In practice R<sub>thj-a</sub> will be determined by customer's PCB characteristics. 125°C/W when mounted on a minimum pad of 2 oz. copper.  
 3. 100% tested by conditions of L=0.1mH, I<sub>AS</sub>=5A, V<sub>GS</sub>=10V, V<sub>DD</sub>=50V, rated 100V

**Characteristics (Tc=25°C, unless otherwise specified)**

| Symbol                 | Min. | Typ. | Max. | Unit | Test Conditions   |
|------------------------|------|------|------|------|---|
| <b>Static</b>          |      |      |      |      |   |
| BV <sub>DSS</sub>      | 100  | -    | -    | V    | V <sub>GS</sub> =0V, I <sub>D</sub> =250μA                      |
| V <sub>GS(th)</sub>    | 1    | -    | 2.5  |      | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA       |
| G <sub>FS</sub> *1     | -    | 7.8  | -    | S    | V <sub>DS</sub> =10V, I <sub>D</sub> =7A                        |
| I <sub>GSS</sub>       | -    | -    | ±100 | nA   | V <sub>GS</sub> =±20V   |
| I <sub>DSS</sub>       | -    | -    | 1    | μA   | V <sub>DS</sub> =80V, V <sub>GS</sub> =0V                       |
|                        | -    | -    | 10   |      | V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>j</sub> =85°C |
| R <sub>DS(ON)</sub> *1 | -    | 163  | 210  | mΩ   | V <sub>GS</sub> =10V, I <sub>D</sub> =10A                       |
|                        | -    | 178  | 235  |      | V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A                      |
| <b>Dynamic</b>         |      |      |      |      |   |
| C <sub>iss</sub>       | -    | 258  | -    | pF   | V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz               |
| C <sub>oss</sub>       | -    | 38   | -    |      |   |
| C <sub>rss</sub>       | -    | 25   | -    |      |   |
| Q <sub>g</sub> *1, 2   | -    | 6.3  | -    | nC   | V <sub>DS</sub> =80V, V <sub>GS</sub> =10V, I <sub>D</sub> =10A |
| Q <sub>gs</sub> *1, 2  | -    | 1.1  | -    |      |   |
| Q <sub>gd</sub> *1, 2  | -    | 3.0  | -    |      |   |

**Characteristics (Tc=25°C, unless otherwise specified)**

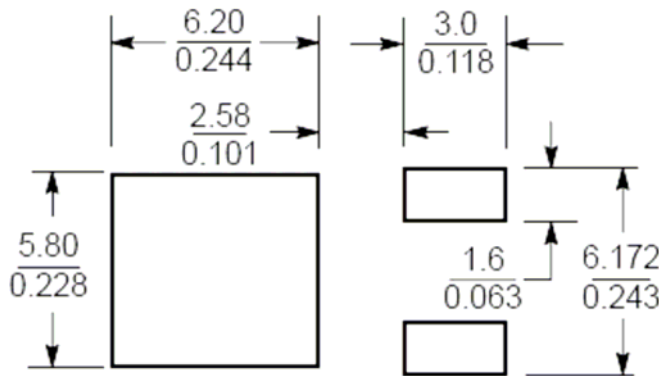
| Symbol                   | Min. | Typ. | Max. | Unit | Test Conditions   |
|--------------------------|------|------|------|------|---|
| Qg *1,2                  | -    | 2.7  | -    | nC   | V <sub>DS</sub> =50V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A                     |
| Qgs *1,2                 | -    | 2.2  | -    |      |   |
| Qgd *1,2                 | -    | 0.1  | -    |      |   |
| t <sub>d(ON)</sub> *1,2  | -    | 4.6  | -    | ns   | V <sub>DS</sub> =50V, I <sub>D</sub> =1A, V <sub>GS</sub> =10V, R <sub>GS</sub> =6Ω |
| t <sub>r</sub> *1,2      | -    | 16.6 | -    |      |   |
| t <sub>d(OFF)</sub> *1,2 | -    | 18.2 | -    |      |   |
| t <sub>f</sub> *1,2      | -    | 16.8 | -    |      |   |
| R <sub>g</sub>           | -    | 3.1  | -    | Ω    | f=1MHz  |

**Source-Drain Diode**

|                    |   |      |     |    |  |
|--------------------|---|------|-----|----|--|
| I <sub>S</sub> *1  | - | -    | 7   | A  |  |
| I <sub>SM</sub> *3 | - | -    | 28  |    |  |
| V <sub>SD</sub> *1 | - | 0.91 | 1.2 | V  | I <sub>S</sub> =10A, V <sub>GS</sub> =0V         |
| t <sub>rr</sub>    | - | 35   | -   | ns | I <sub>F</sub> =10A, dI <sub>F</sub> /dt=100A/μs |
| Q <sub>rr</sub>    | - | 35   | -   | nC |  |

Note : \*1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%  
 \*2.Independent of operating temperature  
 \*3.Pulse width limited by maximum junction temperature.

**Recommended soldering footprint**

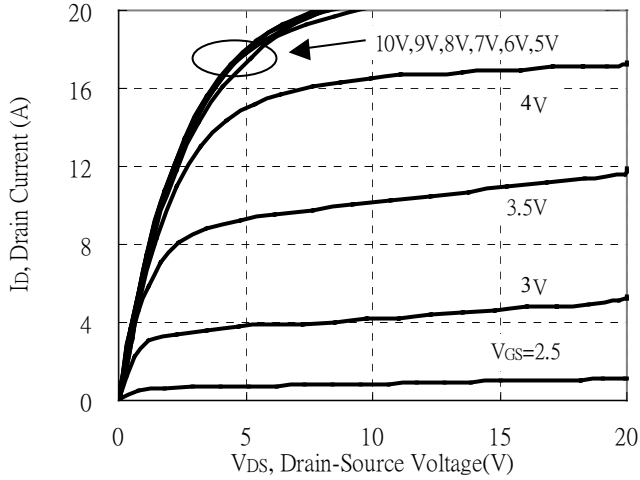


Unit (  $\frac{\text{mm}}{\text{inch}}$  )

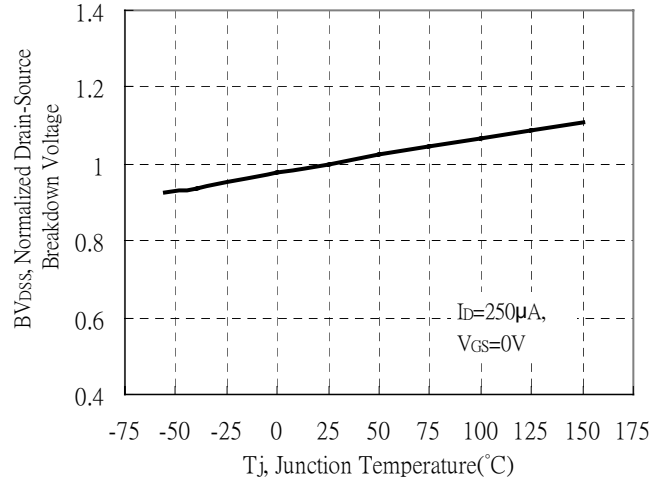


**Typical Characteristics**

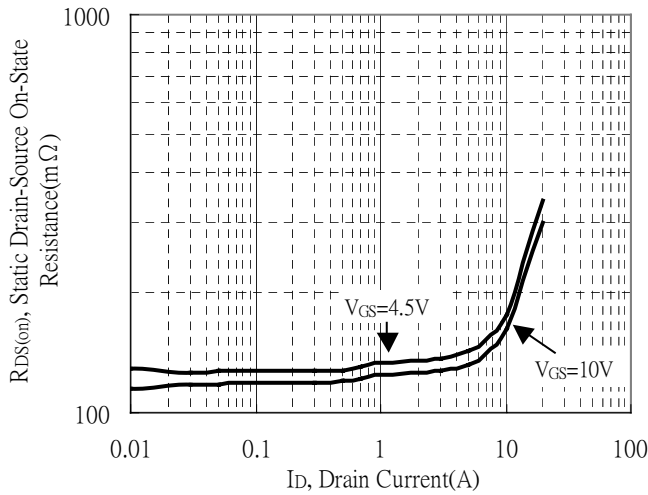
Typical Output Characteristics



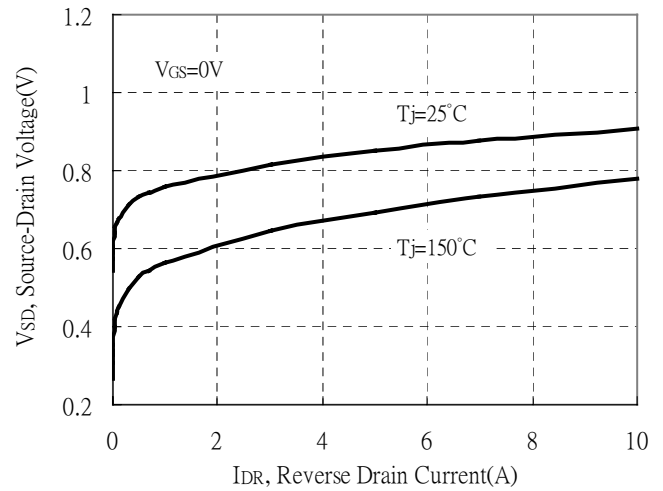
Brekdown Voltage vs Ambient Temperature



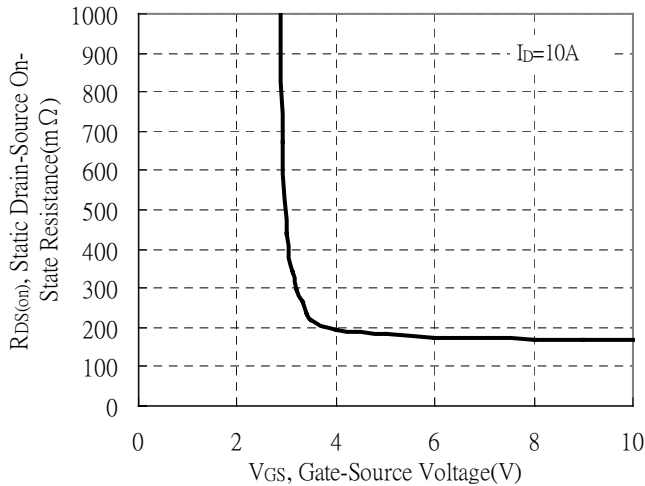
Static Drain-Source On-State resistance vs Drain Current



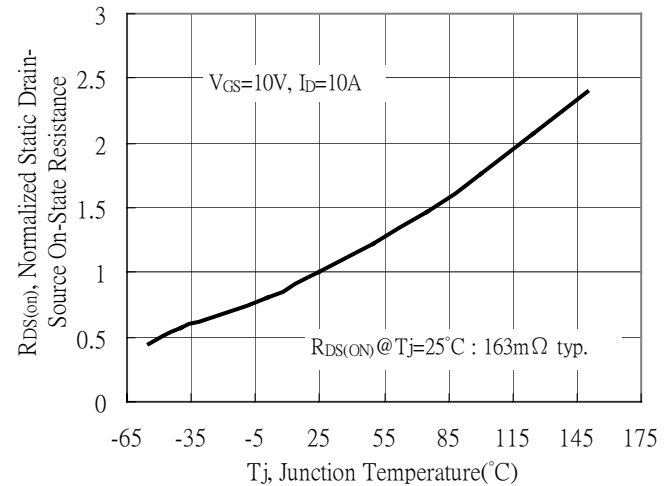
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

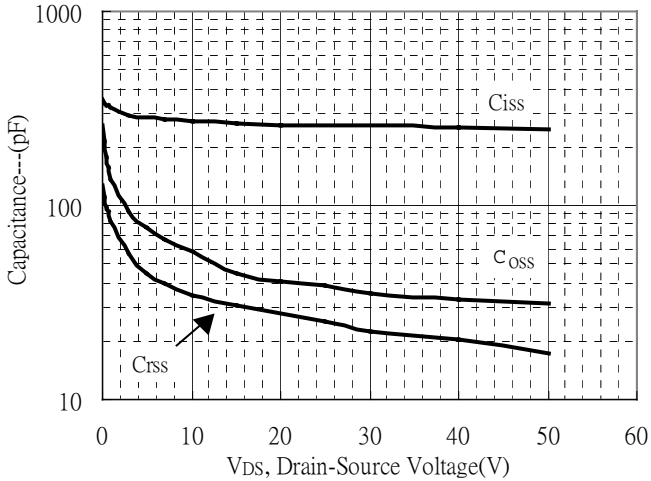


Drain-Source On-State Resistance vs Junction Temperature

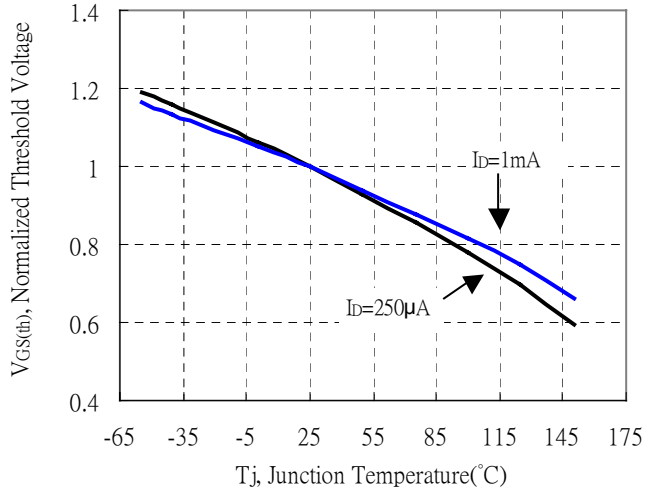


**Typical Characteristics(Cont.)**

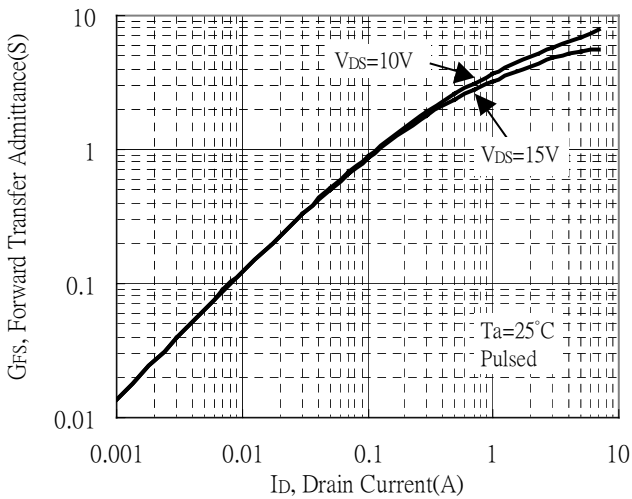
Capacitance vs Drain-to-Source Voltage



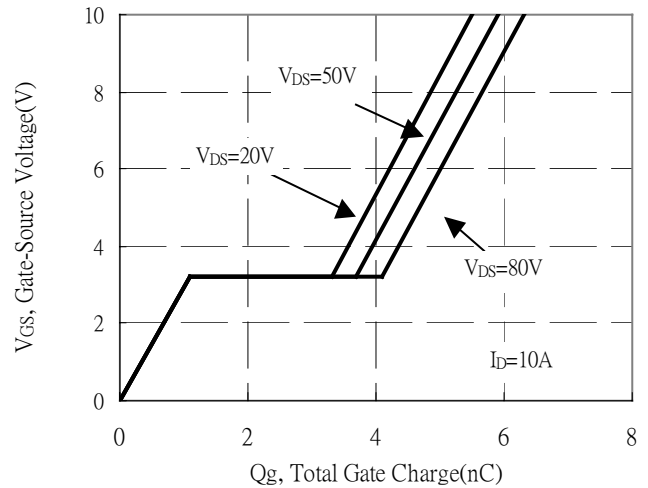
Threshold Voltage vs Junction Temperature



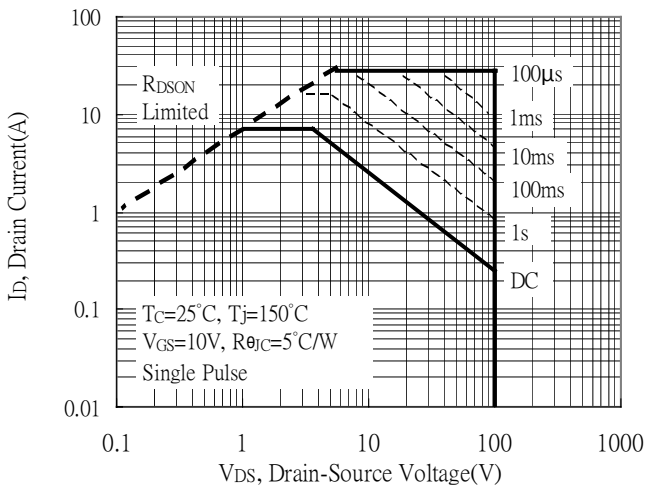
Forward Transfer Admittance vs Drain Current



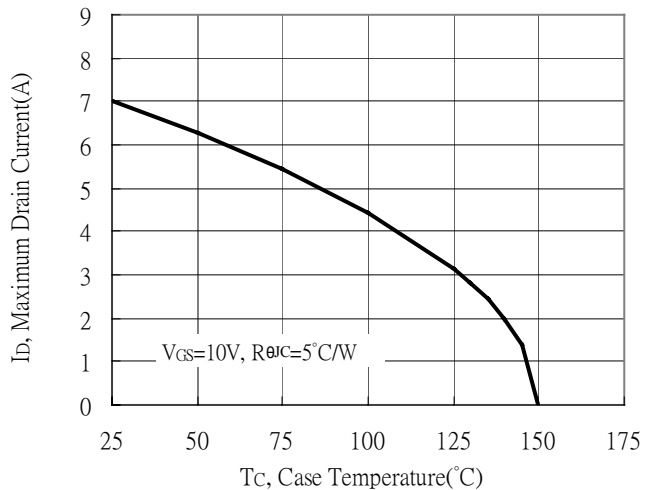
Gate Charge Characteristics



Maximum Safe Operating Area



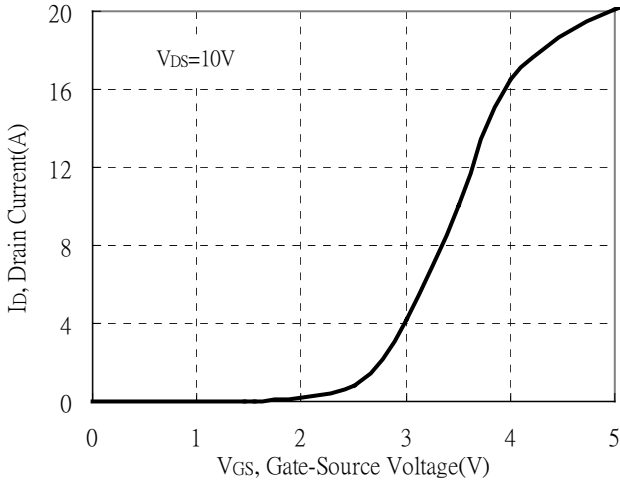
Maximum Drain Current vs Case Temperature



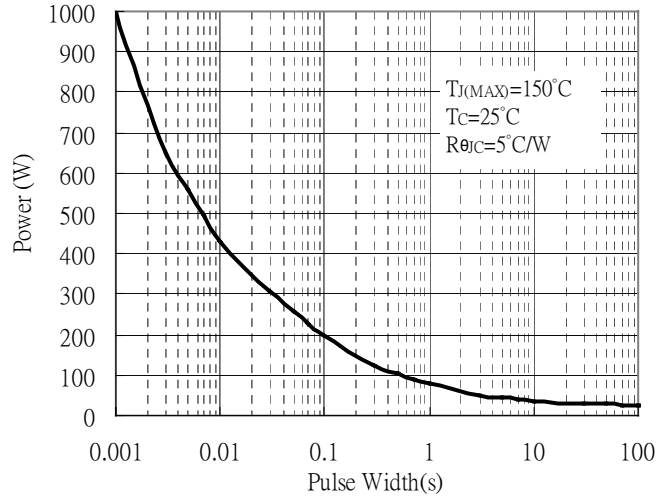


**Typical Characteristics(Cont.)**

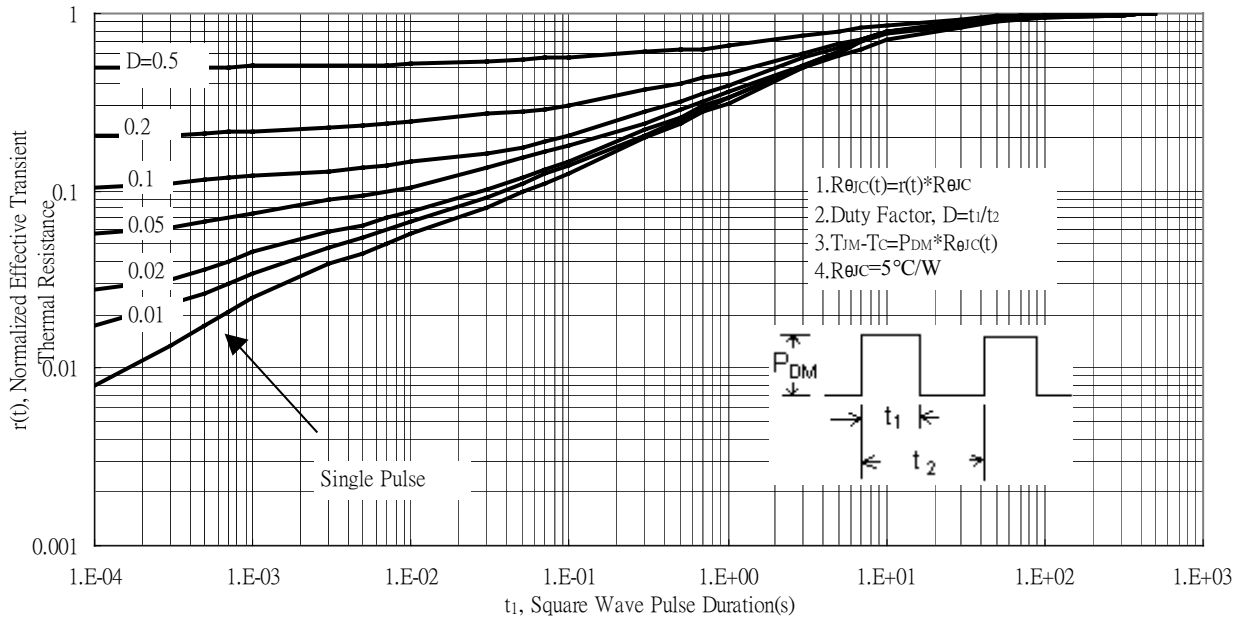
Typical Transfer Characteristics



Single Pulse Power Rating, Junction to Case



Transient Thermal Response Curves

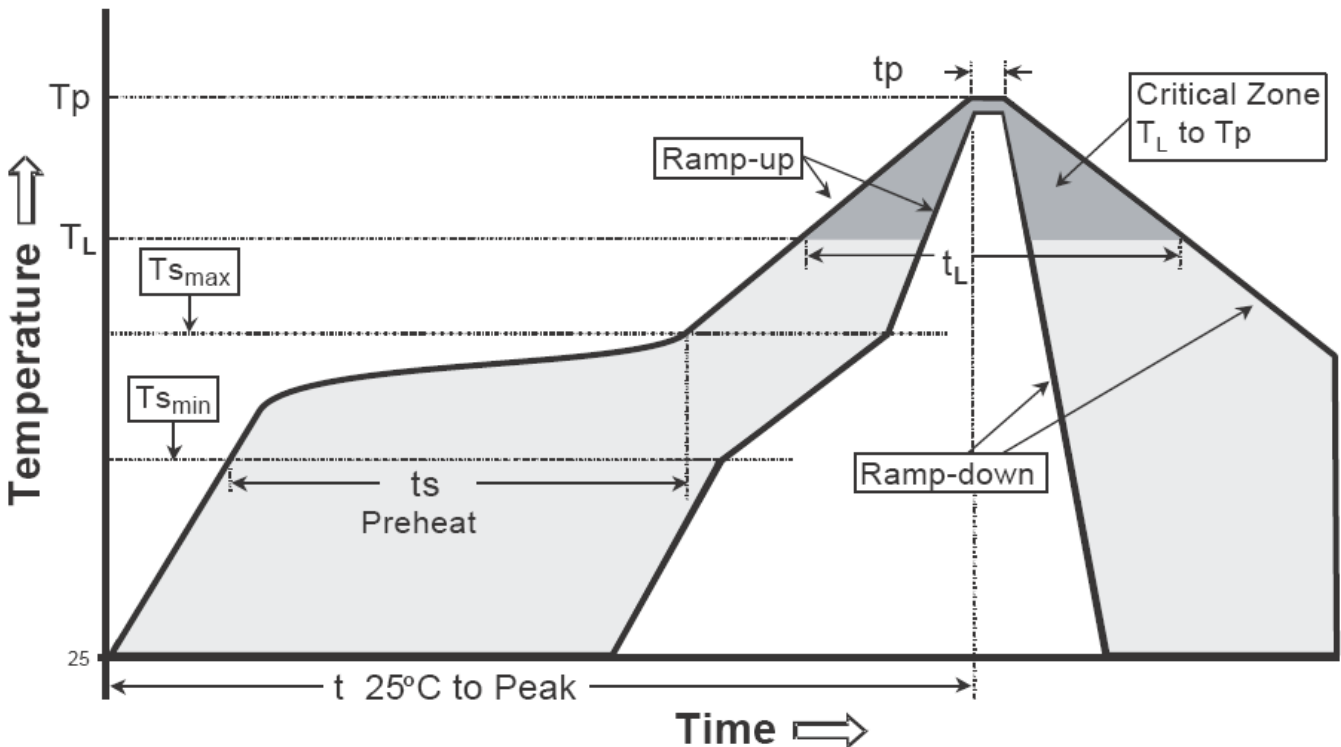




**Recommended wave soldering condition**

|                 |                  |                 |
|-----------------|------------------|-----------------|
| Product         | Peak Temperature | Soldering Time  |
| Pb-free devices | 260 +0/-5 °C     | 5 +1/-1 seconds |

**Recommended temperature profile for IR reflow**

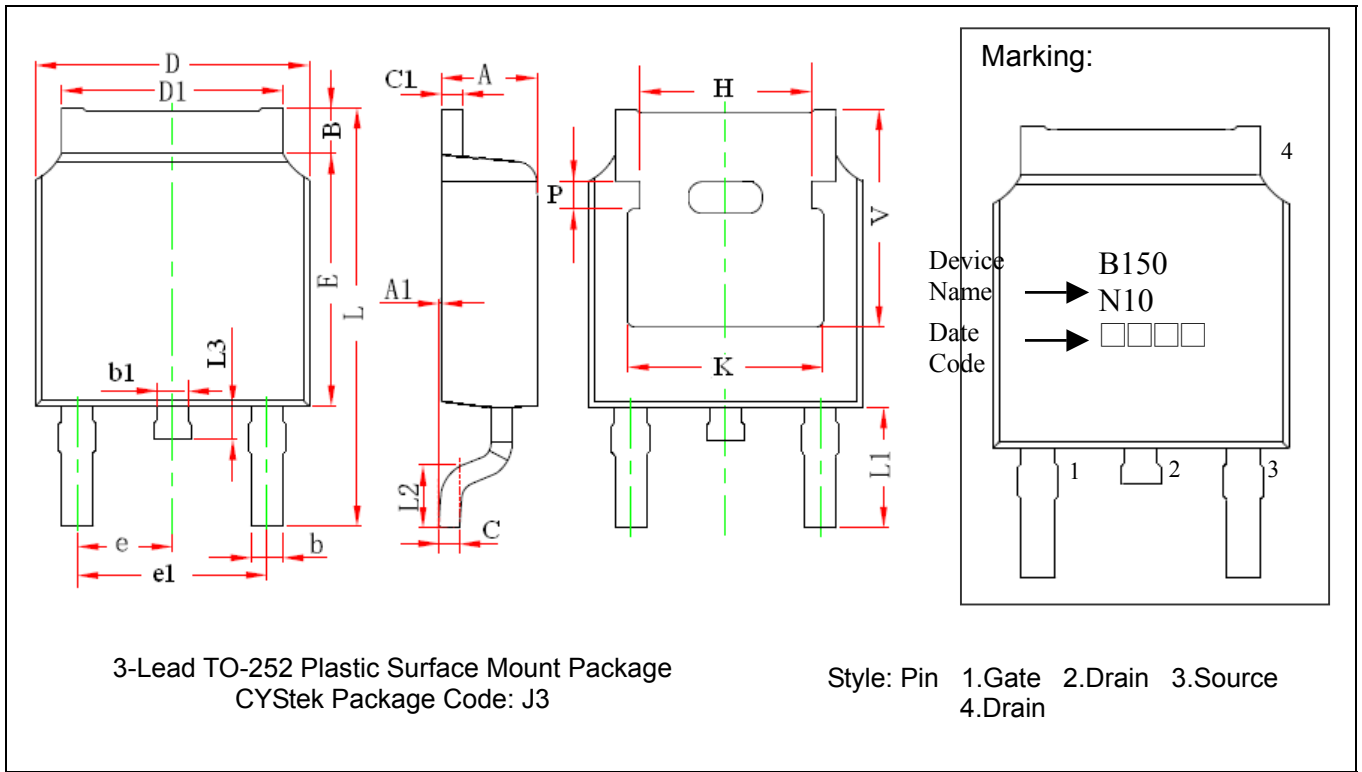


| Profile feature                                | Sn-Pb eutectic Assembly | Pb-free Assembly |
|--|-------------------------|------------------|
| Average ramp-up rate (Tsmax to Tp)             | 3°C/second max.         | 3°C/second max.  |
| Preheat  |                         |                  |
| -Temperature Min(Ts min)                       | 100°C                   | 150°C            |
| -Temperature Max(Ts max)                       | 150°C                   | 200°C            |
| -Time(ts min to ts max)                        | 60-120 seconds          | 60-180 seconds   |
| Time maintained above:                         |                         |                  |
| -Temperature (TL)                              | 183°C                   | 217°C            |
| - Time (tL)                                    | 60-150 seconds          | 60-150 seconds   |
| Peak Temperature(TP)                           | 240 +0/-5 °C            | 260 +0/-5 °C     |
| Time within 5°C of actual peak temperature(tp) | 10-30 seconds           | 20-40 seconds    |
| Ramp down rate                                 | 6°C/second max.         | 6°C/second max.  |
| Time 25 °C to peak temperature                 | 6 minutes max.          | 8 minutes max.   |

Note : All temperatures refer to topside of the package, measured on the package body surface.



**TO-252 Dimension**



| DIM | Inches |       | Millimeters |       | DIM | Inches |       | Millimeters |        |
|-----|--------|-------|-------------|-------|-----|--------|-------|-------------|--------|
|     | Min.   | Max.  | Min.        | Max.  |     | Min.   | Max.  | Min.        | Max.   |
| A   | 0.087  | 0.094 | 2.200       | 2.400 | e   | 0.086  | 0.094 | 2.186       | 2.386  |
| A1  | 0.000  | 0.005 | 0.000       | 0.127 | e1  | 0.172  | 0.188 | 4.372       | 4.772  |
| B   | 0.039  | 0.048 | 0.990       | 1.210 | H   | 0.163  | REF   | 4.140       | REF    |
| b   | 0.026  | 0.034 | 0.660       | 0.860 | K   | 0.190  | REF   | 4.830       | REF    |
| b1  | 0.026  | 0.034 | 0.660       | 0.860 | L   | 0.386  | 0.409 | 9.800       | 10.400 |
| C   | 0.018  | 0.023 | 0.460       | 0.580 | L1  | 0.114  | REF   | 2.900       | REF    |
| C1  | 0.018  | 0.023 | 0.460       | 0.580 | L2  | 0.055  | 0.067 | 1.400       | 1.700  |
| D   | 0.256  | 0.264 | 6.500       | 6.700 | L3  | 0.024  | 0.039 | 0.600       | 1.000  |
| D1  | 0.201  | 0.215 | 5.100       | 5.460 | P   | 0.026  | REF   | 0.650       | REF    |
| E   | 0.236  | 0.244 | 6.000       | 6.200 | V   | 0.211  | REF   | 5.350       | REF    |

**Notes:** 1.Controlling dimension: millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead : Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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